

SILICON BRIDGE RECTIFIERS	<p>REVERSE VOLTAGE - 50 to 1000Volts FORWARD CURRENT - 4.0 Amperes</p> <p style="text-align: center;">GBU-C</p> <p style="text-align: center;">Dimensions in inches and (millimeters)</p>
----------------------------------	--

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.
Single phase, half wave ,60Hz, resistive or inductive load.
For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	GBU 4005C	GBU 401C	GBU 402C	GBU 404C	GBU 406C	GBU 408C	GBU 410C	UNIT	
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V	
Maximum RMS Voltage	V _{RMS}	30	70	140	280	420	560	700	V	
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V	
Maximum Average Forward Rectified Current @ T _c =100°C (without heatsink)	I _(AV)					4.0				A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load (JEDEC Method)	I _{FSM}					150				A
Maximum Forward Voltage at 4.0A DC	V _F					1.0				V
Maximum DC Reverse Current at Rated DC Blocking Voltage @ T _J =25°C @ T _J =125°C	I _R					10.0				uA
I ² t Rating for Fusing (t<8.3ms)	I ² t					93				A ² s
Typical Junction Capacitance Per Element (Note1)	C _J					45				pF
Typical Thermal Resistance (Note2)	R _{θJC}					2.2				°C/W
Operating Temperature Range	T _J					-55 to +125				°C
Storage Temperature Range	T _{STG}					-55 to +150				°C

NOTES: 1.Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
2.Device mounted on 50mm*50mm*1.6mm cu plate heatsink.

FIG.1-FORWARD CURRENT DERATING CURVE

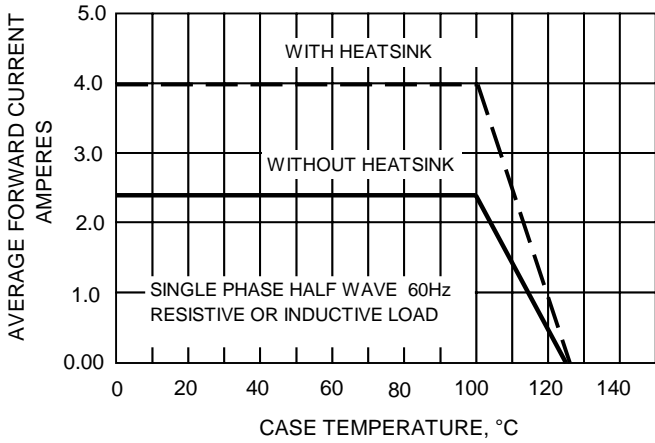


FIG.2-MAXIMUM NON-REPETITIVE SURGE CURRENT

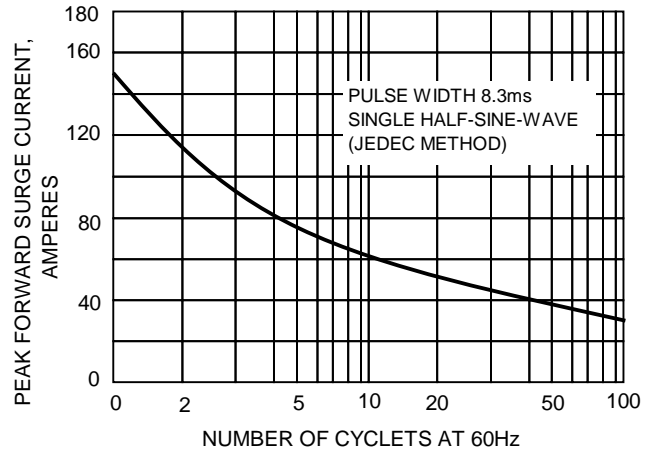


FIG.3-TYPICAL JUNCTION CAPACITANCE

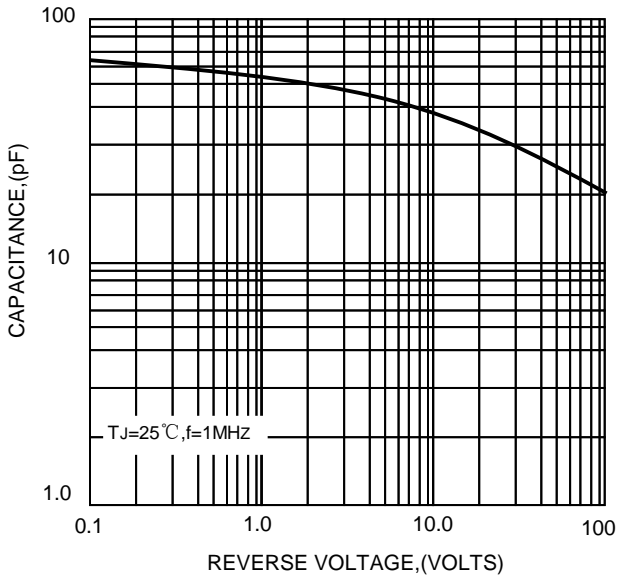


FIG.4-TYPICAL FORWARD CHARACTERISTICS

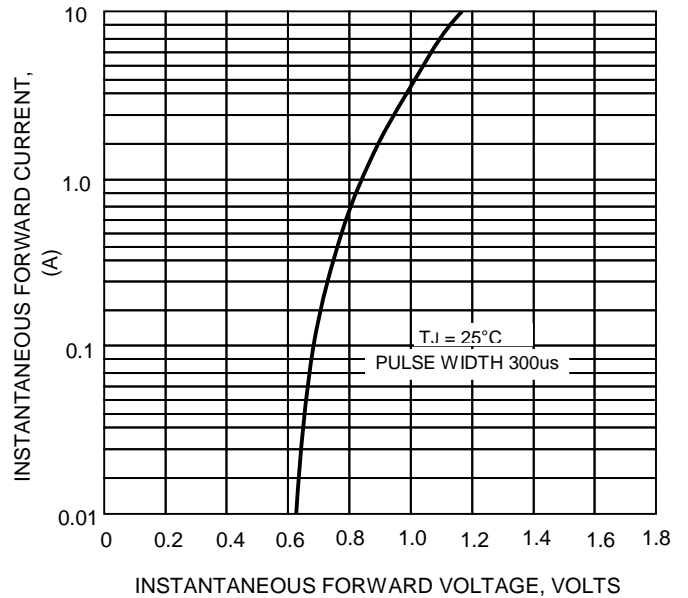


FIG.5-TYPICAL REVERSE CHARACTERISTICS

